27LV256

256K (32K x 8) Low-Voltage CMOS EPROM

FEATURES

- Wide voltage range 3.0V to 5.5V
- High speed performance
  - 200 ns access time available at 3.0V
- CMOS Technology for low power consumption
  - 8 mA Active current at 3.0V
  - 20 mA Active current at 5.5V
  - 100 µA Standby current
- Factory programming available
- Auto-insertion-compatible plastic packages
- Auto ID aids automated programming
- Separate chip enable and output enable controls
- High speed "Express" programming algorithm
- Organized 32K x 8: JEDEC standard pinouts
  - 28-pin Dual-in-line package
  - 32-pin PLCC package
  - 28-pin SOIC package
  - Tape and reel
- Data Retention > 200 years
- Available for the following temperature ranges:
  - Commercial: 0˚C to +70˚C
  - Industrial: -40˚C to +85˚C

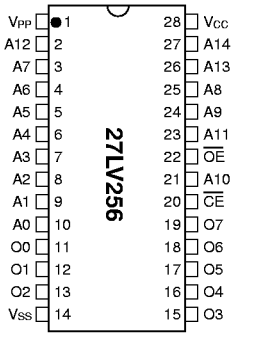
DESCRIPTION

The Microchip Technology Inc. 27LV256 is a low voltage (3.0 volt) CMOS EPROM designed for battery powered applications. The device is organized as a 32K x 8 (32K-Byte) non-volatile memory product. The 27LV256 consumes only 8 mA maximum of active current during a 3.0 volt read operation therefore improving battery performance. This device is designed for very low voltage applications where conventional 5.0 volt only EPROMS can not be used. Accessing individual bytes from an address transition or from power-up (chip enable pin going low) is accomplished in less than 200 ns at 3.0V. This device allows systems designers the ability to use low voltage non-volatile memory with today's' low voltage microprocessors and peripherals in battery powered applications.

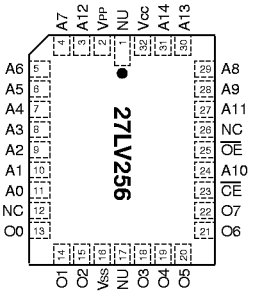
A complete family of packages is offered to provide the most flexibility in applications. For surface mount applications, PLCC or SOIC packaging is available. Tape and reel packaging is also available for PLCC or SOIC packages.

PACKAGE TYPES

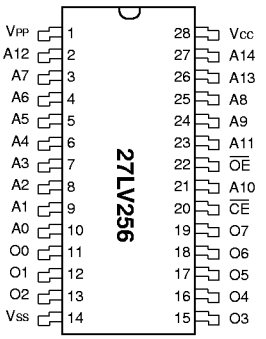
PDIP



PLCC



SOIC



1.0 ELECTRICAL CHARACTERISTICS

1.1 Maximum Ratings*

V_{CC} and input voltages w.r.t. V_{SS} ..... -0.6V to +7.25V

V_{PP} voltage w.r.t. V_{SS} during programming ..... -0.6V to +14V

Voltage on A9 w.r.t. V_{SS}..... -0.6V to +13.5V

Output voltage w.r.t. V_{SS}.....-0.6V to V_{CC} +1.0V

Storage temperature ..... -65˚C to +150˚C

Ambient temp. with power applied..... -65˚C to +125˚C

*Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
A0-A14	Address Inputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
V_{PP}	Programming Voltage
O0 - O7	Data Output
V_{CC}	+5V or +3V Power Supply
V_{SS}	Ground
NC	No Connection; No Internal Connection
NU	Not Used; No External Connection Is Allowed

TABLE 1-2: READ OPERATION DC CHARACTERISTICS

			V_{CC} = +5V ±10% or 3.0V where indicated Commercial: Tamb = 0˚C to +70˚C Industrial: Tamb = -40˚C to +85˚C				
Parameter	**Part***	**Status**	**Symbol**	**Min.**	**Max.**	**Units**	**Conditions**
Input Voltages	all	Logic "1" Logic "0"	V_{IH} V_{IL}	2.0 -0.5	V_{CC}+1 0.8	V V	
Input Leakage	all		I_{LI}	-10	10	µA	V_{IN} = 0 to V_{CC}
Output Voltages	all	Logic "1" Logic "0"	V_{OH} V_{OL}	2.4	 0.45	V V	I_{OH} = -400 µA I_{OL} = 2.1 mA
Output Leakage	all	—	I_{LO}	-10	10	µA	V_{OUT} = 0V to V_{CC}
Input Capacitance	all	—	C_{IN}	—	6	pF	V_{IN} = 0V; Tamb = 25°C; f = 1 MHz
Output Capacitance	all	—	C_{OUT}	—	12	pF	V_{OUT} = 0V; Tamb = 25°C; f = 1 MHz
Power Supply Current, Active	C I	TTL input TTL input	I_{CC1} I_{CC2}	— —	20 @ 5.0V 8 @ 3.0V 25 @ 5.0V 10 @ 3.0V	mA mA mA mA	V_{CC} = 5.5V; V_{PP} = V_{CC} f = 1 MHz; $\overline{OE}$ = $\overline{CE}$ = V_{IL}; I_{OUT} = 0 mA; V_{IL} = -0.1 to 0.8V; V_{IH} = 2.0 to V_{CC}; Note 1
Power Supply Current, Standby	C I all	TTL input TTL input CMOS input	$I_{CC(S)}$	—	1 @ 3.0V 2 @ 3.0V 100 @ 3.0V	mA mA µA	 $\overline{CE}$=V_{CC} ± 0.2V

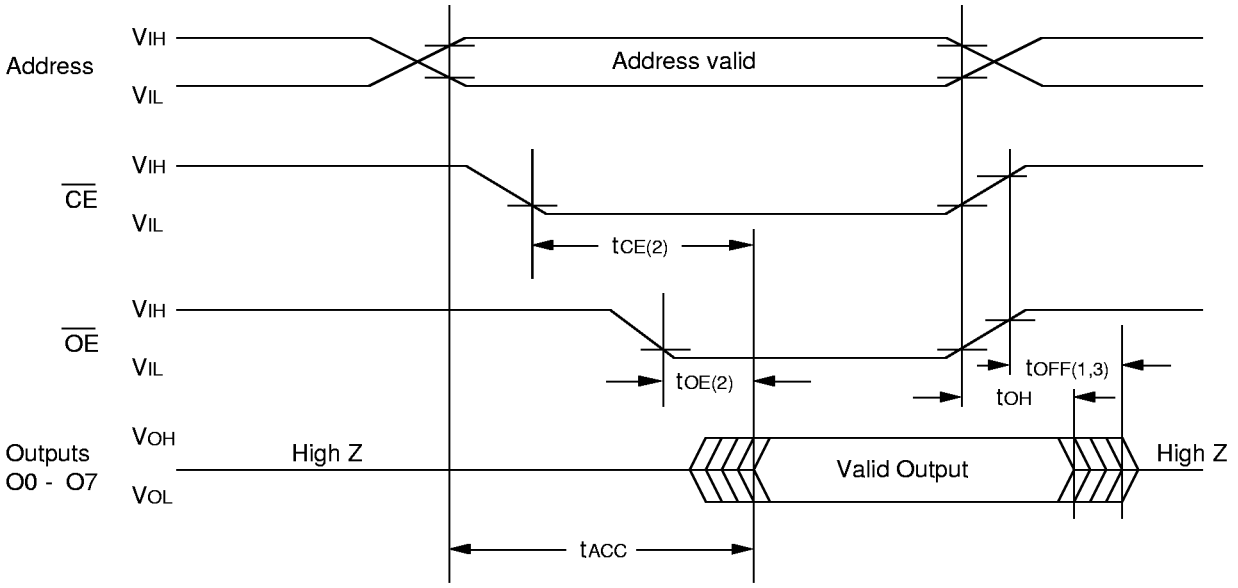
* Parts: C=Commercial Temperature Range
I =Industrial Temperature Ranges

Note 1: Typical active current increases .75 mA per MHz up to operating frequency for all temperature ranges.

TABLE 1-3: READ OPERATION AC CHARACTERISTICS

AC Testing Waveform: V_{IH} = 2.4V and V_{IL} = 0.45V; V_{OH} = 2.0V V_{OL} = 0.8V Output Load: 1 TTL Load + 100 pF Input Rise and Fall Times: 10 ns Ambient Temperature: Commercial: Tamb = 0°C to +70°C Industrial: Tamb = -40°C to +85°C									
Parameter	**Sym**	**27HC256-20**		**27HC256-25**		**27HC256-30**		**Units**	**Conditions**
		Min	**Max**	**Min**	**Max**	**Min**	**Max**		
Address to Output Delay	t_{ACC}	—	200	—	250	—	300	ns	$\overline{CE}$ = $\overline{OE}$ = V_{IL}
$\overline{CE}$ to Output Delay	t_{CE}	—	200	—	250	—	300	ns	$\overline{OE}$ = V_{IL}
$\overline{OE}$ to Output Delay	t_{OE}	—	100	—	125	—	125	ns	$\overline{CE}$ = V_{IL}
$\overline{CE}$ or $\overline{OE}$ to O/P High Impedance	t_{OFF}	0	50	0	50	0	50	ns	
Output Hold from Address $\overline{CE}$ or $\overline{OE}$, whichever goes first	t_{OH}	0	—	0	—	0	—	ns	

FIGURE 1-1: READ WAVEFORMS



Notes: (1) t_{OFF} is specified for $\overline{OE}$ or $\overline{CE}$, whichever occurs first
(2) $\overline{OE}$ may be delayed up to t_{CE} - t_{OE} after the falling edge of $\overline{CE}$ without impact on t_{CE}
(3) This parameter is sampled and is not 100% tested.

TABLE 1-4: PROGRAMMING DC CHARACTERISTICS

			Ambient Temperature: Tamb = 25°C ± 5°C VCC = 6.5V ± 0.25V, VPP = 13.0V ± 0.25V			
Parameter	**Status**	**Symbol**	**Min**	**Max.**	**Units**	**Conditions**
Input Voltages	Logic"1" Logic"0"	VIH VIL	2.0 -0.1	VCC+1 0.8	V V	
Input Leakage	—	ILI	-10	10	µA	VIN = 0V to VCC
Output Voltages	Logic"1" Logic"0"	VOH VOL	2.4	 0.45	V V	IOH = -400 µA IOL = 2.1 mA
VCC Current, program & verify	—	ICC2	—	20	mA	Note 1
VPP Current, program	—	IPP2	—	25	mA	Note 1
A9 Product Identification	—	VH	11.5	12.5	V	

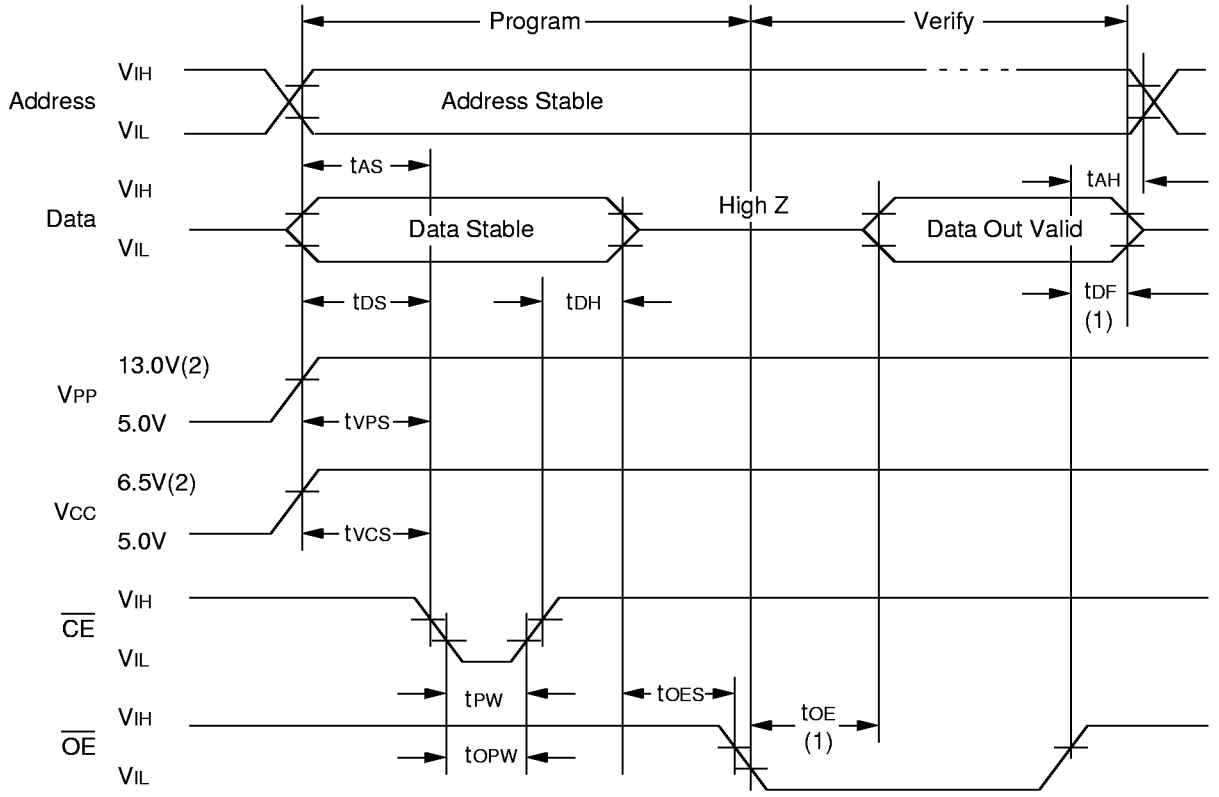
Note 1: VCC must be applied simultaneously or before VPP and removed simultaneously or after VPP.

TABLE 1-5: PROGRAMMING AC CHARACTERISTICS

for Program, Program Verify and Program Inhibit Modes	AC Testing Waveform: VIH=2.4V and VIL=0.45V; VOH=2.0V; VOL=0.8V Output Load: 1 TLL Load + 100pF Ambient Temperature: Tamb=25°C±5°C VCC= 6.5V ± 0.25V, VPP =13.0V ± 0.25V				
Parameter	**Symbol**	**Min.**	**Max.**	**Units**	**Remarks**
Address Set-Up Time	tAS	2	—	µs	
Data Set-Up Time	tDS	2	—	µs	
Data Hold Time	tDH	2	—	µs	
Address Hold Time	tAH	0	—	µs	
Float Delay (2)	tDF	0	130	ns	
VCC Set-Up Time	tVCS	2	—	µs	
Program Pulse Width (1)	tPW	95	105	µs	100 µs typical
$\overline{CE}$ Set-Up Time	tCES	2	—	µs	
$\overline{OE}$ Set-Up Time	tOES	2	—	µs	
VPP Set-Up Time	tVPS	2	—	µs	
Data Valid from $\overline{OE}$	tOE	—	100	ns	

Note 1: For express algorithm, initial programming width tolerance is 100 µs ±5%.
2: This parameter is only sampled and not 100% tested. Output float is defined as the point where data is no longer driven (see timing diagram).

FIGURE 1-2: PROGRAMMING WAVEFORMS



Notes: (1) t_{DF} and t_{OE} are characteristics of the device but must be accommodated by the programmer
(2) V_{CC} = 6.5V ±0.25V, V_{PP} = V_H = 13.0V ±0.25V for express algorithm

TABLE 1-6: MODES

Operation Mode	$\overline{CE}$	$\overline{OE}$	V_{PP}	A9	O0 - O7
Read	V_{IL}	V_{IL}	V_{CC}	X	D_{OUT}
Program	V_{IL}	V_{IH}	V_H	X	D_{IN}
Program Verify	V_{IH}	V_{IL}	V_H	X	D_{OUT}
Program Inhibit	V_{IH}	V_{IH}	V_H	X	High Z
Standby	V_{IH}	X	V_{CC}	X	High Z
Output Disable	V_{IL}	V_{IH}	V_{CC}	X	High Z
Identity	V_{IL}	V_{IL}	V_{CC}	V_H	Identity Code

X = Don't Care

1.2 Read Mode

(See Timing Diagrams and AC Characteristics)

Read Mode is accessed when:

a) the $\overline{CE}$ pin is low to power up (enable) the chip
b) the $\overline{OE}$ pin is low to gate the data to the output pins

For Read operations, if the addresses are stable, the address access time (t_{ACC}) is equal to the delay from $\overline{CE}$ to output (t_{CE}). Data is transferred to the output after a delay from the falling edge of $\overline{OE}$ (t_{OE}).

1.3 Standby Mode

The standby mode is defined when the $\overline{CE}$ pin is high (V_{IH}) and a program mode is not defined. Output Disable

1.4 Output Enable

This feature eliminates bus contention in multiple bus microprocessor systems and the outputs go to a high impedance when the following condition is true:

- The $\overline{OE}$ pin is high and program mode is not defined.

1.5 Programming Mode

The Express algorithm has been developed to improve on the programming throughput times in a production environment. Up to 10 100-microsecond pulses are applied until the byte is verified. No over-programming is required. A flowchart of the express algorithm is shown in Figure 1.

Programming takes place when:

a) V_{CC} is brought to the proper voltage
b) V_{PP} is brought to the proper V_H level
c) the $\overline{OE}$ pin is high
d) the $\overline{CE}$ pin is low

Since the erased state is "1" in the array, programming of "0" is required. The address to be programmed is set via pins A0-A14 and the data to be programmed is presented to pins O0-O7. When data and address are stable, a low-going pulse on the $\overline{CE}$ line programs that location.

1.6 Verify

After the array has been programmed it must be verified to ensure that all the bits have been correctly programmed. This mode is entered when all of the following conditions are met:

a) V_{CC} is at the proper level
b) V_{PP} is at the proper V_H level
c) the $\overline{CE}$ pin is high
d) the $\overline{OE}$ line is low

1.7 Inhibit

When Programming multiple devices in parallel with different data, only $\overline{CE}$ needs to be under separate control to each device. By pulsing the $\overline{CE}$ line low on a particular device, that device will be programmed, and all other devices with $\overline{CE}$ held high will not be programmed with the data although address and data are available on their input pins.

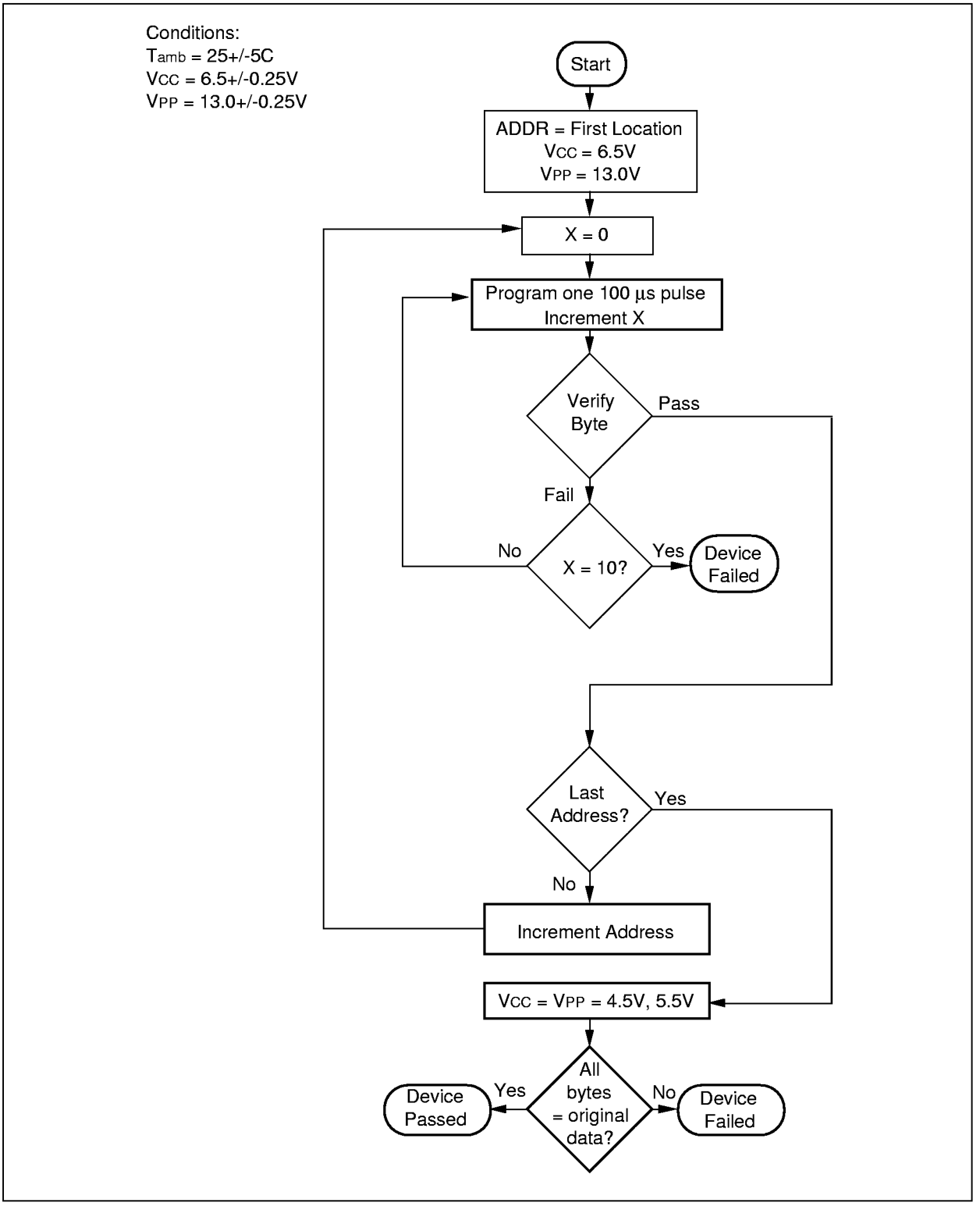
1.8 Identity Mode

In this mode specific data is outputted which identifies the manufacturer as Microchip Technology Inc. and device type. This mode is entered when Pin A9 is taken to V_H (11.5V to 12.5V). The $\overline{CE}$ and $\overline{OE}$ lines must be at V_{IL}. A0 is used to access any of the two non-erasable bytes whose data appears on O0 through O7.

Pin	Input	Output								
Identity → ↓	A0	O7	O6	O5	O4	O3	O2	O1	O0	Hex
Manufacturer	V_{IL}	0	0	1	0	1	0	0	1	29
Device Type*	V_{IH}	1	0	0	0	1	1	0	0	8C

* Code subject to change.

FIGURE 1-3: PROGRAMMING EXPRESS ALGORITHM



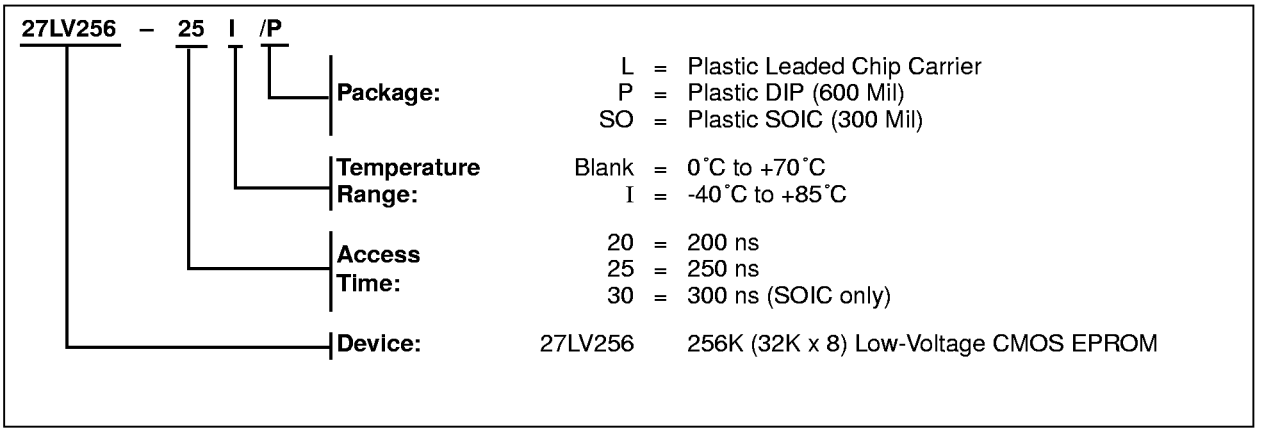
NOTES:

NOTES:

NOTES:

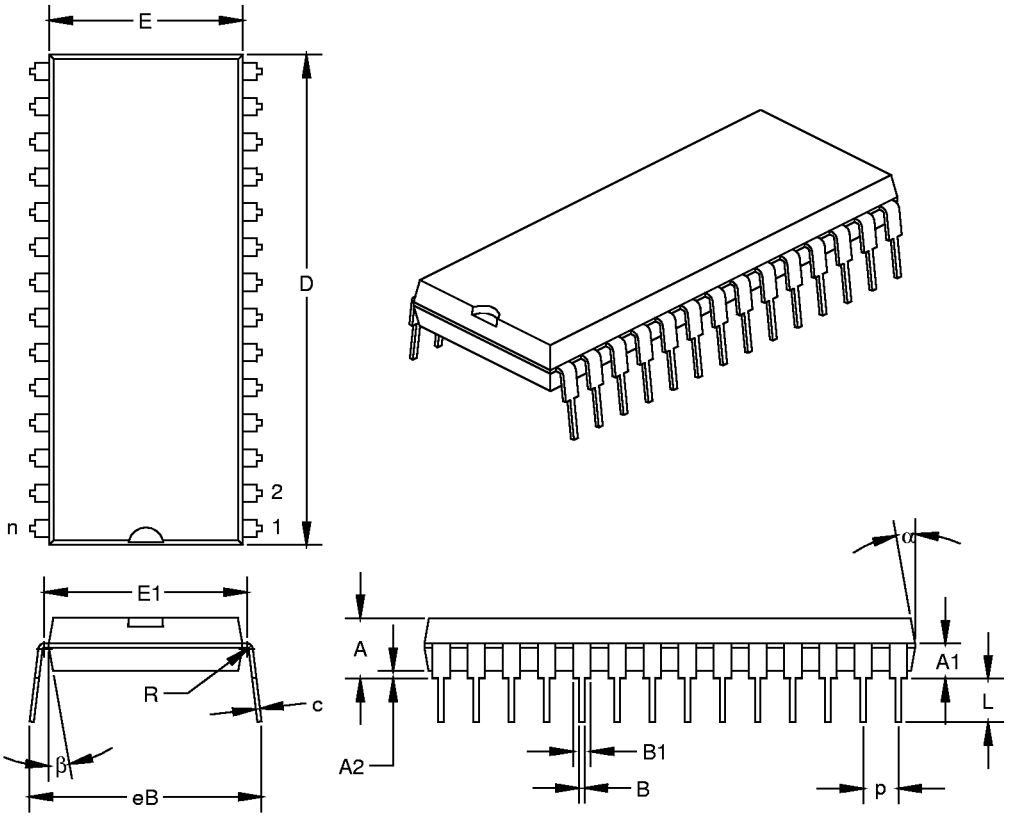
27LV256 Product Identification System

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.



Packaging Diagrams and Parameters

Package Type: K04-079 28-Lead Plastic Dual In-line (P) – 600 mil



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
PCB Row Spacing			0.600			15.24	
Number of Pins	n		28			28	
Pitch	p		0.100			2.54	
Lower Lead Width	B	0.014	0.016	0.018	0.36	0.41	0.46
Upper Lead Width	B1†	0.040	0.050	0.060	1.02	1.27	1.52
Shoulder Radius	R	0.000	0.005	0.010	0.00	0.13	0.25
Lead Thickness	c	0.008	0.012	0.015	0.20	0.29	0.38
Top to Seating Plane	A	0.160	0.173	0.185	4.06	4.38	4.70
Top of Lead to Seating Plane	A1	0.081	0.101	0.121	2.04	2.55	3.06
Base to Seating Plane	A2	0.015	0.023	0.030	0.38	0.57	0.76
Tip to Seating Plane	L	0.115	0.125	0.135	2.92	3.18	3.43
Package Length	D‡	1.380	1.395	1.465	35.05	35.43	37.20
Molded Package Width	E‡	0.505	0.550	0.555	12.80	13.97	14.10
Radius to Radius Width	E1	0.567	0.577	0.587	14.40	14.66	14.91
Overall Row Spacing	eB	0.640	0.660	0.680	16.26	16.76	17.27
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter.

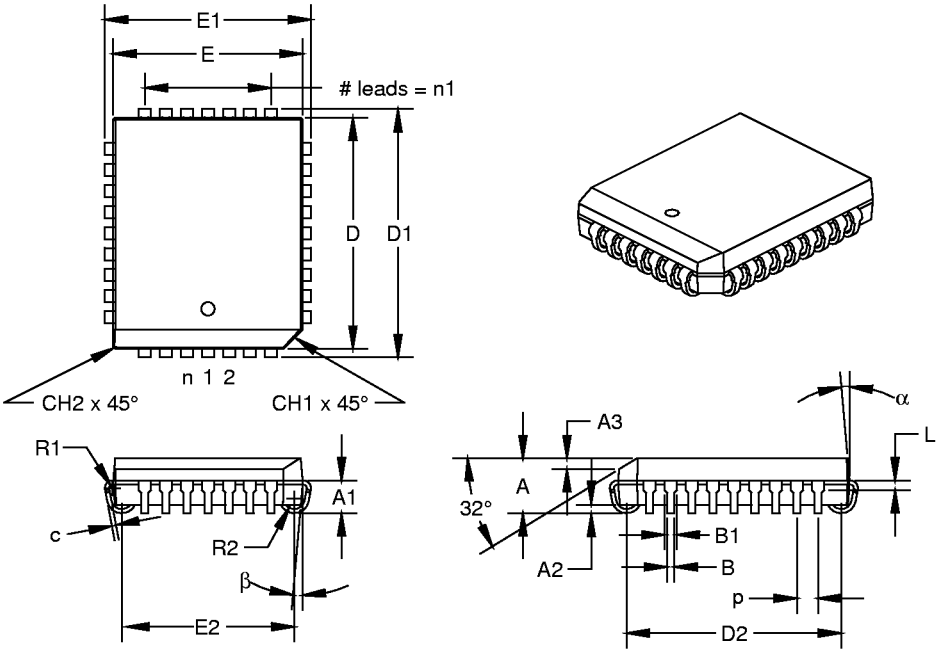
† Dimension “B1” does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003” (0.076 mm) per side or 0.006” (0.152 mm) more than dimension “B1.”

‡ Dimensions “D” and “E” do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010” (0.254 mm) per side or 0.020” (0.508 mm) more than dimensions “D” or “E.”

JEDEC equivalent: MS-011 AB

Packaging Diagrams and Parameters

Package Type: K04-023 32-Lead Plastic Leaded Chip Carrier (L) – Rectangle



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		32			32	
Pitch	p		0.050			1.27	
Overall Pack. Height	A	0.127	0.131	0.135	3.23	3.33	3.43
Shoulder Height	A1	0.060	0.078	0.095	1.52	1.97	2.41
Standoff	A2	0.015	0.020	0.025	0.38	0.51	0.64
Side 1 Chamfer Dim.	A3	0.021	0.026	0.031	0.53	0.66	0.79
Corner Chamfer (1)	CH1	0.035	0.045	0.055	0.89	1.14	1.40
Corner Chamfer (other)	CH2	0.000	0.005	0.010	0.00	0.13	0.25
Overall Pack. Width	E1	0.485	0.490	0.495	12.32	12.45	12.57
Overall Pack. Length	D1	0.585	0.590	0.595	14.86	14.99	15.11
Molded Pack. Width	E‡	0.447	0.450	0.453	11.35	11.43	11.51
Molded Pack. Length	D‡	0.547	0.550	0.553	13.89	13.97	14.05
Footprint Width	E2	0.380	0.410	0.440	9.65	10.41	11.18
Footprint Length	D2	0.480	0.510	0.540	12.19	12.95	13.72
Pins along Width	n1		7			7	
Lead Thickness	c	0.008	0.010	0.012	0.20	0.25	0.30
Upper Lead Width	B1†	0.026	0.029	0.032	0.66	0.74	0.81
Lower Lead Width	B	0.013	0.017	0.021	0.33	0.43	0.53
Upper Lead Length	L	0.010	0.020	0.030	0.25	0.51	0.76
Shoulder Inside Radius	R1	0.003	0.008	0.013	0.08	0.20	0.33
J-Bend Inside Radius	R2	0.020	0.025	0.030	0.51	0.64	0.76
Mold Draft Angle Top	α	0	5	10	0	5	10
Mold Draft Angle Bottom	β	0	5	10	0	5	10

* Controlling Parameter.

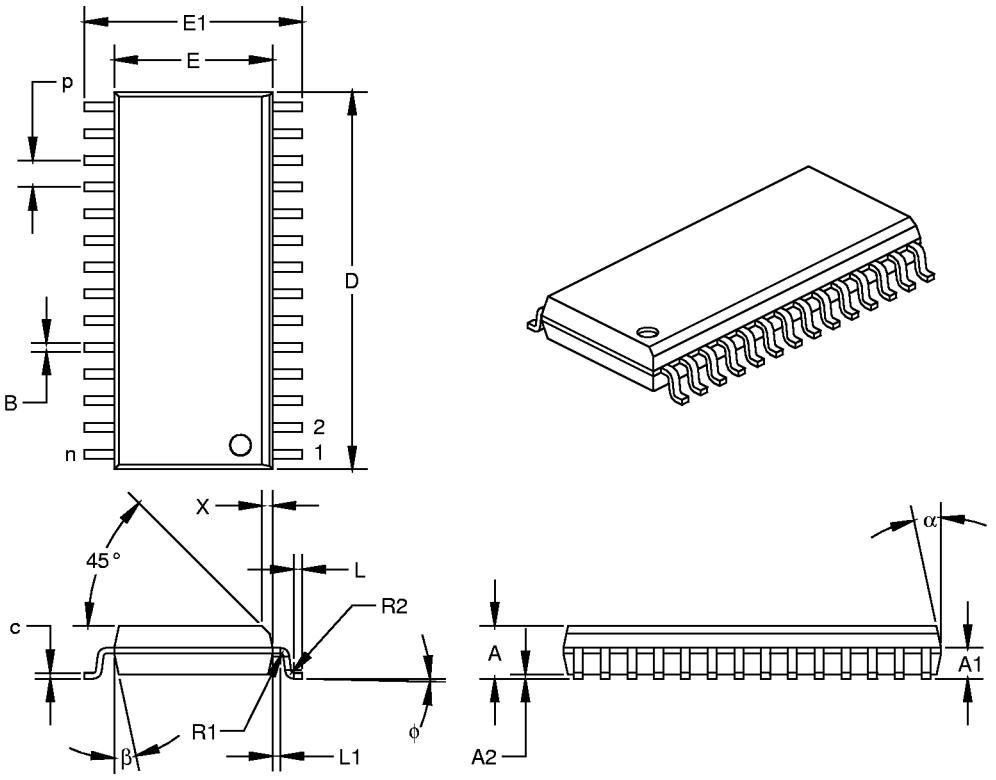
† Dimension "B1" does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003" (0.076 mm) per side or 0.006" (0.152 mm) more than dimension "B1."

‡ Dimensions "D" and "E" do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010" (0.254 mm) per side or 0.020" (0.508 mm) more than dimensions "D" or "E."

JEDEC equivalent: MS-016 AE

Packaging Diagrams and Parameters

Package Type: K04-052 28-Lead Plastic Small Outline (SO) – Wide, 300 mil



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Pitch	p		0.050			1.27	
Number of Pins	n		28			28	
Overall Pack. Height	A	0.093	0.099	0.104	2.36	2.50	2.64
Shoulder Height	A1	0.048	0.058	0.068	1.22	1.47	1.73
Standoff	A2	0.004	0.008	0.011	0.10	0.19	0.28
Molded Package Length	D‡	0.700	0.706	0.712	17.78	17.93	18.08
Molded Package Width	E‡	0.292	0.296	0.299	7.42	7.51	7.59
Outside Dimension	E1	0.394	0.407	0.419	10.01	10.33	10.64
Chamfer Distance	X	0.010	0.020	0.029	0.25	0.50	0.74
Shoulder Radius	R1	0.005	0.005	0.010	0.13	0.13	0.25
Gull Wing Radius	R2	0.005	0.005	0.010	0.13	0.13	0.25
Foot Length	L	0.011	0.016	0.021	0.28	0.41	0.53
Foot Angle	φ	0	4	8	0	4	8
Radius Centerline	L1	0.010	0.015	0.020	0.25	0.38	0.51
Lead Thickness	c	0.009	0.011	0.012	0.23	0.27	0.30
Lower Lead Width	B†	0.014	0.017	0.019	0.36	0.42	0.48
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

* Controlling Parameter.

† Dimension “B” does not include dam-bar protrusions. Dam-bar protrusions shall not exceed 0.003” (0.076 mm) per side or 0.006” (0.152 mm) more than dimension “B.”

‡ Dimensions “D” and “E” do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010” (0.254 mm) per side or 0.020” (0.508 mm) more than dimensions “D” or “E.”

JEDEC equivalent: MS-013 AE